

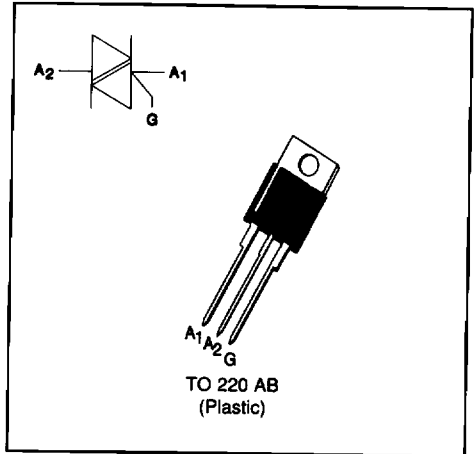
STANDARD TRIACS

FEATURES

- HIGH SURGE CURRENT CAPABILITY
- COMMUTATION : $(dv/dt)_c > 10V/\mu s$
- BTA Family :
INSULATING VOLTAGE = 2500V(RMS)
(UL RECOGNIZED : E81734)

DESCRIPTION

The BTA/BTB16 B triac family are high performance glass passivated PNPN devices. These parts are suitable for general purpose applications where high surge current capability is required. Application such as phase control and static switching on inductive or resistive load.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
I _{T(RMS)}	RMS on-state current (360° conduction angle)	BTA T _c = 80 °C	16	A
		BTB T _c = 90 °C		
I _{TSM}	Non repetitive surge peak on-state current (T _J initial = 25°C)	tp = 8.3 ms	170	A
		tp = 10 ms	160	
I _{2t}	I _{2t} value	tp = 10 ms	128	A _{2s}
di/dt	Critical rate of rise of on-state current Gate supply : I _G = 500mA di _G /dt = 1A/μs	Repetitive F = 50 Hz	10	A/μs
		Non Repetitive	50	
T _{stg} T _J	Storage and operating junction temperature range		- 40 to + 150 - 40 to + 125	°C °C
TI	Maximum lead temperature for soldering during 10 s at 4.5 mm from case		230	°C

Symbol	Parameter	BTA / BTB16... B				Unit
		400	600	700	800	
V _{DRM} V _{RRM}	Repetitive peak off-state voltage T _J = 125 °C	400	600	700	800	V

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth (j-a)	Junction to ambient	60	°C/W
Rth (j-c) DC	Junction to case for DC	BTA	2.9
		BTB	2.3
Rth (j-c) AC	Junction to case for 360° conduction angle (F = 50 Hz)	BTA	2.2
		BTB	1.75

GATE CHARACTERISTICS (maximum values)

P_G (AV) = 1W P_{GM} = 40W (tp = 20 μs) I_{GM} = 6A (tp = 20 μs) V_{GM} = 16V (tp = 20 μs).

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Quadrant		Suffix	Unit
					B	
IGT	VD=12V (DC) RL=33Ω	Tj=25°C	I-II-III	MAX	50	mA
			IV	MAX	100	
VGT	VD=12V (DC) RL=33Ω	Tj=25°C	I-II-III-IV	MAX	1.5	V
VGD	VD=VDRM RL=3.3kΩ	Tj=125°C	I-II-III-IV	MIN	0.2	V
igt	VD=VDRM IG = 500mA dIG/dt = 3A/μs	Tj=25°C	I-II-III-IV	TYP	2	μs
IL	IG=1.2 IGT	Tj=25°C	I-III-IV	TYP	40	mA
			II		70	
IH *	IT= 500mA gate open	Tj=25°C		MAX	50	mA
VTM *	ITM= 22.5A tp= 380μs	Tj=25°C		MAX	1.6	V
IDRM IRRM	VDRM Rated VRRM Rated	Tj=25°C		MAX	0.01	mA
		Tj=125°C		MAX	2	
dV/dt *	Linear slope up to VD=67%VDRM gate open	Tj=125°C		MIN	250	V/μs
(dV/dt)c *	(dl/dt)c = 7A/ms	Tj=125°C		MIN	10	V/μs

* For either polarity of electrode A2 voltage with reference to electrode A1.

Fig.1 : Maximum RMS power dissipation versus RMS on-state current ($F=50\text{Hz}$).
(Curves are cut off by $(di/dt)c$ limitation)

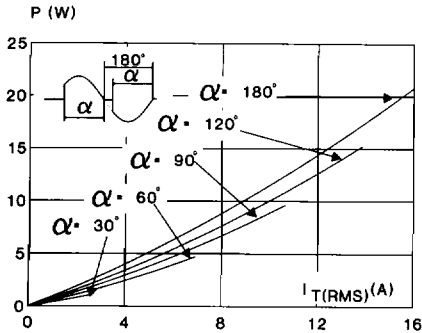


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTA).

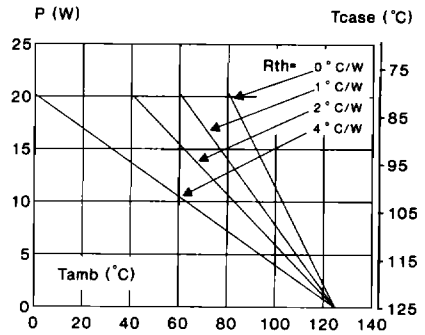


Fig.3 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTB).

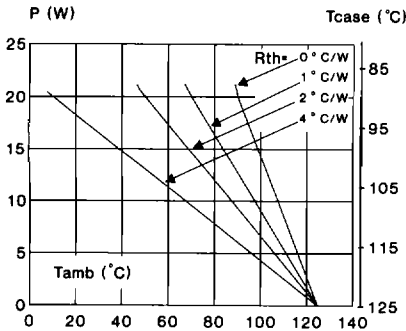


Fig.4 : RMS on-state current versus case temperature.

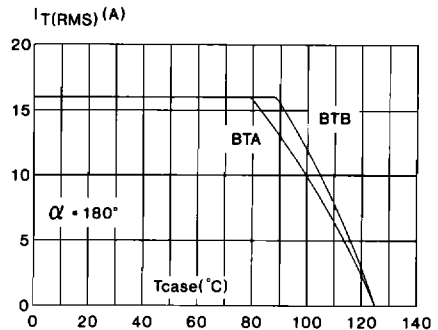


Fig.5 : Thermal transient impedance junction to case and junction to ambient versus pulse duration.
($Z_{th\ j-c}$: BTA version only)

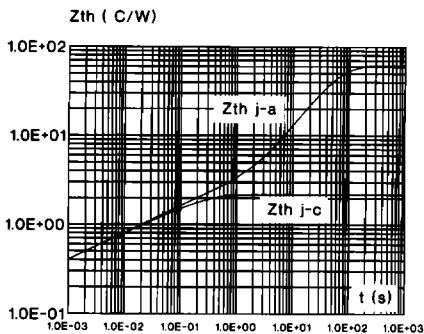


Fig.6 : Relative variation of gate trigger current and holding current versus junction temperature.

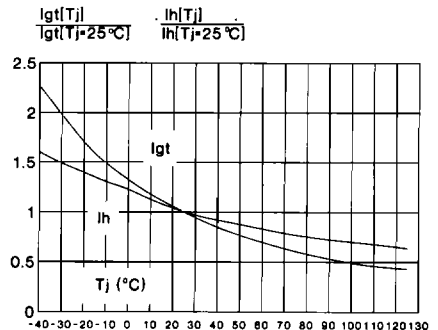


Fig.7 : Non Repetitive surge peak on-state current versus number of cycles.

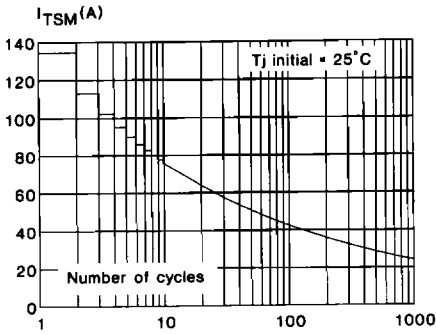


Fig.8 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10\text{ms}$, and corresponding value of I^2t .

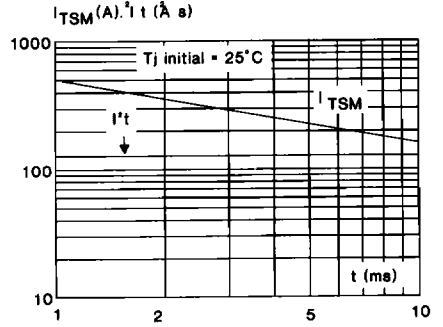
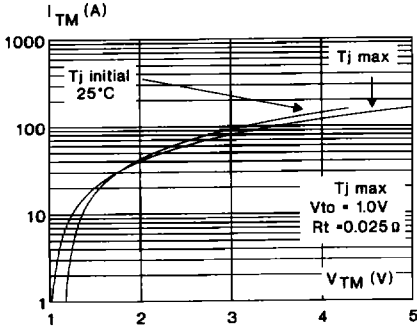
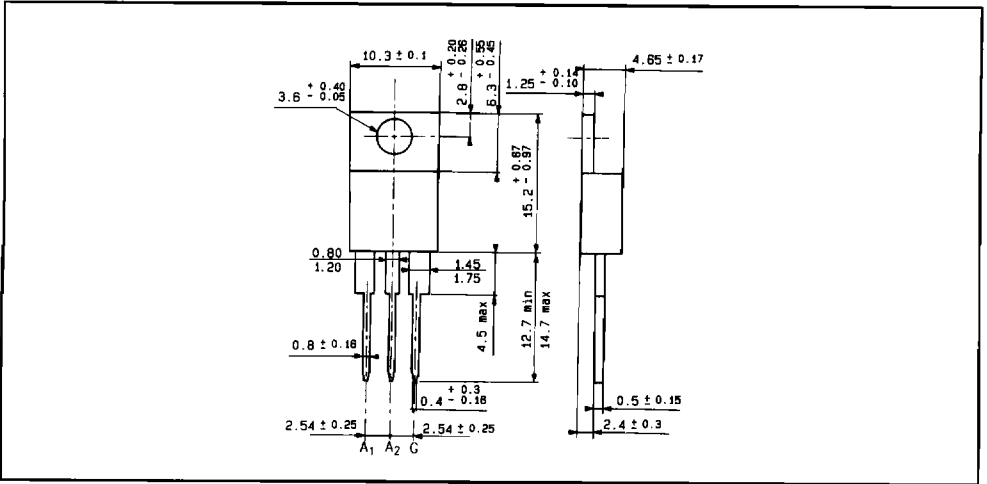


Fig.9 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA (in millimeters)

TO 220 AB Plastic



Cooling method : by conduction (method C)

Marking : type number

Weight : 2 g